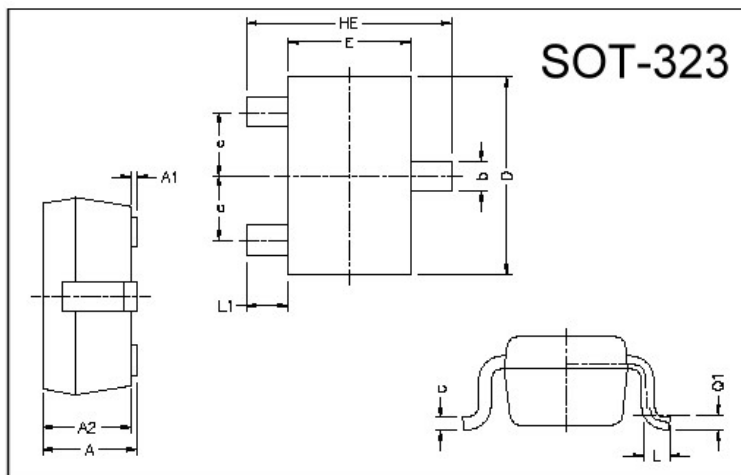
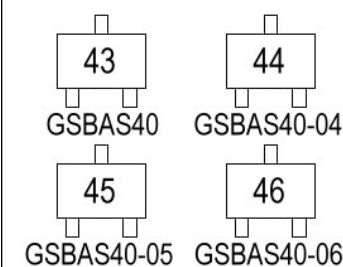
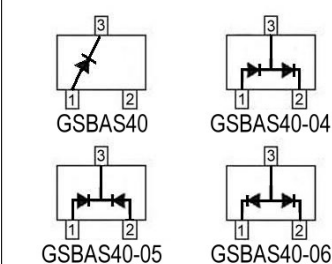


GSBAS40 thru GSBAS40-06**SURFACE MOUNT, SCHOTTKY BARRIER DIODE****VOLTAGE 40V, CURRENT 0.2A****Description**

These schottky barrier diodes are designed for high speed switching applications, circuit protection and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Package Dimensions

| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 0.80 | 1.10 | L1 | 0.42 | REF. |
| A1 | 0 | 0.10 | L | 0.15 | 0.35 |
| A2 | 0.80 | 1.00 | b | 0.25 | 0.40 |
| D | 1.80 | 2.20 | c | 0.10 | 0.25 |
| E | 1.15 | 1.35 | e | 0.65 | REF. |
| HE | 1.80 | 2.40 | Q1 | 0.15 | BCS. |

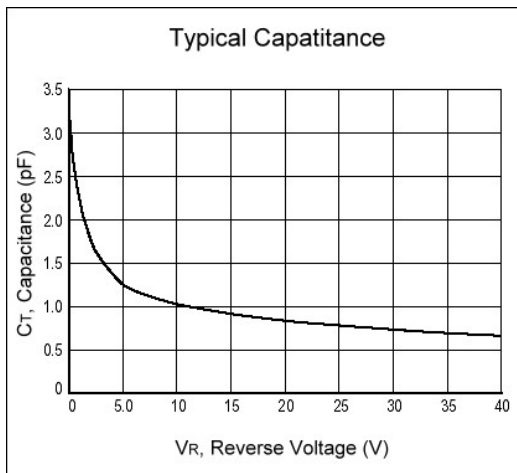
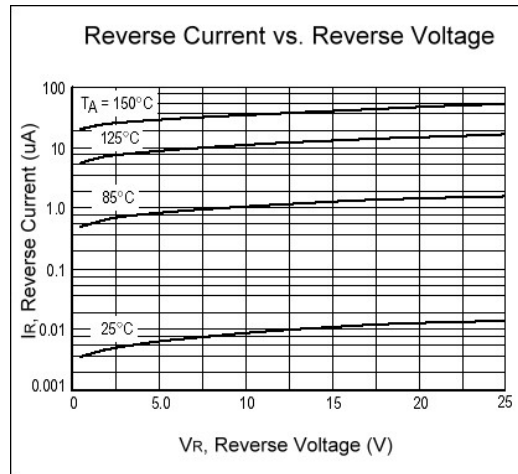
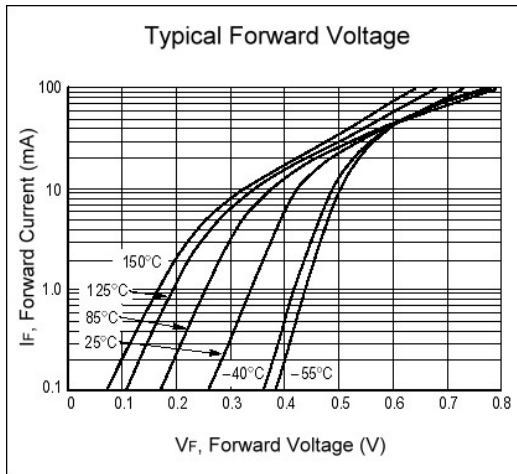
Marking :**Diagram :****Absolute Maximum Ratings at TA = 25°C**

| Parameter | Symbol | Ratings | Unit |
|--|------------------|------------|------|
| Operating Junction Temperature | T _J | -55 ~ +125 | °C |
| Storage Temperature | T _{stg} | -55 ~ +150 | °C |
| Maximum Repetitive Peak Reverse Voltage | V _{RRM} | 40 | V |
| Thermal Resistance Junction to Ambient Air | R _{θJA} | 445 | °C/W |
| Peak Forward Surge Current at tp < 1.0s | I _{FSM} | 0.6 | A |
| Maximum Average Forward Rectified Current | I _o | 0.2 | A |
| Total Power Dissipation | PD | 225 | mW |

Electrical Characteristics (at TA = 25°C unless otherwise noted)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------------------|--------------------|------|------|------|------|------------------------------|
| Reverse Breakdown Voltage | V _{(BR)R} | 40 | - | - | V | IR=10μA |
| Forward Voltage(tp < 300uS) | V _F | - | - | 380 | mV | IF1=1mA |
| | | - | - | 1000 | | IF2=40mA |
| Reverse Leakage Current | I _R | - | - | 200 | nA | VR=30V |
| Total Capacitance | C _T | - | - | 5.0 | pF | VR=0V, f=1MHz |
| Reverse Recover Time | T _{rr} | - | - | 5.0 | ns | IF=IR=10mA, RL=100Ω, Irr=1mA |

Characteristics Curve



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